

9:00 9:05 opening remark

No.	start	end	category	presenter	affiliation	presentation title
1	9:05	9:40	invited	Misako Morota	AIST	Crystal controlled spin pumping effect and interface stability of CoFeB/Sb ₂ Te ₃ bilayers
2	9:40	10:00	general	Simon Wredh	SUTD	Design of a Multi-level Phase-change Optical Switch
3	10:00	10:20	general	Paul Fons	Keio Univ.	Theoretical Investigation of the properties of the Stable and Metastable phases of MnTe
4	10:20	10:40	general	Mihyeon Kim	Tohoku Univ.	Raman study of polymorphic-manganese telluride thin film
break	10:40	10:50				
5	10:50	11:10	general	Serina Ozawa	Tohoku Univ.	Local structure change and the piezoresistivity of MnTe ₂ thin film in tensile testing
6	11:10	11:30	general	Yinli Wang	Tohoku Univ.	Resistance change during tensile testing in Cr ₂ Ge ₂ Te ₆ film
7	11:30	11:50	general	Hiromori Takahashi	Keio Univ.	Phase transition of a MnTe thin film induced by sub-bandgap single-femtosecond-pulse excitation
8	11:50	12:10	general	Takao Homma	Tohoku Univ.	Ultrafast optical response of SnSe under strong excitation
break	12:10	13:00				
9	13:00	13:35	invited	Hitoshi Kawashima	AIST	Silicon Photonics for Multiport Optical Switches
10	13:35	13:55	general	Hiroaki Ishiharajima	Nagaoka Univ. Technol.	Crystallization behavior of sputter-grown amorphous VO ₂ thin films and the effects of W doping on physical properties
11	13:55	14:15	general	Takuto Onuki	Tokai Univ.	Effect of crystallization of GST on phase transition of VO ₂ film in GST/VO ₂ layered structure
12	14:15	14:35	general	Ryoto Yanagisawa	The Univ. of Tokyo	Planar-type thermoelectric generator with phononic nanostructures formed in a 1 μm-thick Si membrane
13	14:35	14:55	general	Ting Yu Teo	SUTD	About reprogrammable waveguides and their application to optical neural networks
14	14:55	15:15	general	Xinxing Xu	Tokyo Tech	Observation of angular-dependent inverted magnetic hysteresis loop in FeCoN thin films
break	15:15	15:25				
15	15:25	16:00	invited	Takuya Yamamoto	Tohoku Univ.	Optimization of phase change material properties and memory device through numerical simulation and Bayesian optimization
16	16:00	16:20	general	Hiroki Endo	Keio Univ.	Friction coefficients between GST and Water
17	16:20	16:40	general	Bokusui Nakayama	Keio Univ.	Tunable Pheromone Interactions among Microswimmers selfpropelling on a PCM Substrate
18	16:40	17:00	general	Yifei Yin	Sophia Univ.	Fine tuning of switching voltages in a Ge-Te based CBRAM device by RF input
19	17:00	17:20	general	Ryosuke Hamamoto	Osaka Metropolitan Univ.	GST-based Bulk Thermoelectric Materials: High Thermoelectric Performance near Room Temperature
20	17:20	17:40	general	Shin-Young Kang	Tohoku Univ.	Role of Si on Structural and Electrical Properties in Phase Change Material GeTe
21	17:40	18:00	general	Nur Qalishah Adanan	SUTD	About the crystallisation temperature dependence of PCM on the reset power

18:00 18:05 closing remark